



TM08N03MI

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = 30V$ $I_D = 7.8A$

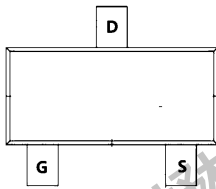
$R_{DS(ON)} = 12 m\Omega$ (Typ.) @ $V_{GS} = 10V$

100% UIS Tested

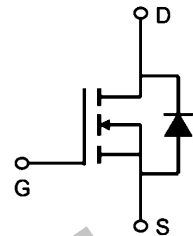
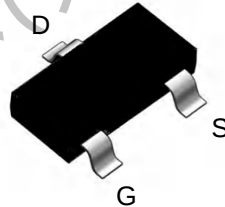
100% R_g Tested



MI:SOT-23-3L



Marking: 3410



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.1	A
I_{DM}	Pulsed Drain Current	28.9	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	170	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	---	$^\circ C/W$

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.9	1.2	1.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	12	18	mΩ
		V _{GS} =4.5V, I _D =5A	-	17	25	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	614	-	pF
C _{oss}	Output Capacitance		-	118	-	pF
C _{rss}	Reverse Transfer Capacitance		-	98	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =11A, V _{GS} =10V	-	16	-	nC
Q _{gs}	Gate-Source Charge		-	2.7	-	nC
Q _{gd}	Gate-Drain (“Miller”) Charge		-	4.5	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, R _L =1.35Ω, R _{GEN} =3Ω, V _{GS} =10V	-	6	-	ns
t _r	Turn-on Rise Time		-	10	-	ns
t _{d(off)}	Turn-off Delay Time		-	30	-	ns
t _f	Turn-off Fall Time		-	6.5	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7.8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =15A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =11A, dI/dt=500A/μs	-	7	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	10	-	nC

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	7.8	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=8A, di/dt=100A/\mu s,$ $T_J=25^\circ C$	---	8	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.9	---	nC

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Figure1: Output Characteristics

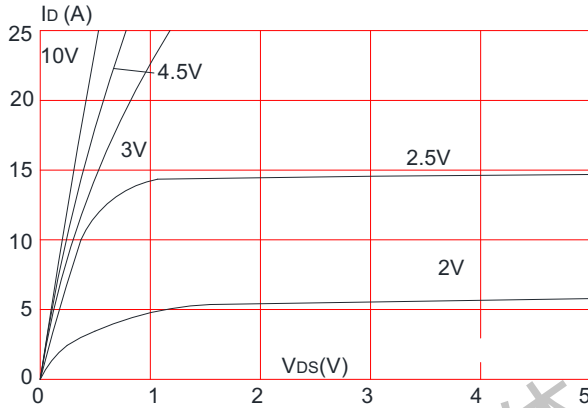


Figure 2: Typical Transfer Characteristics

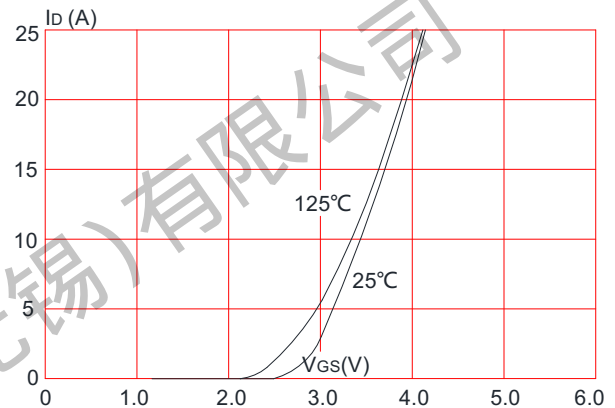


Figure 3: On-resistance vs. Drain Current

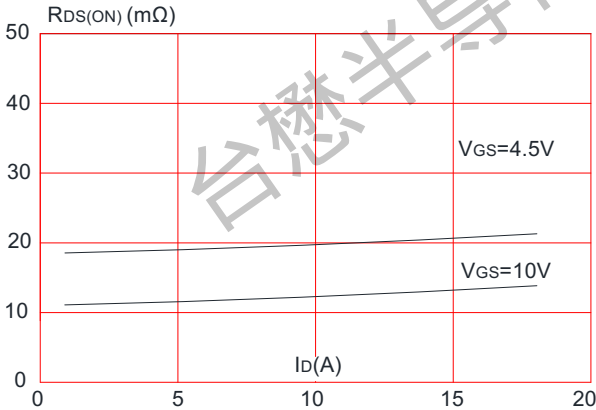


Figure 4: Body Diode Characteristics

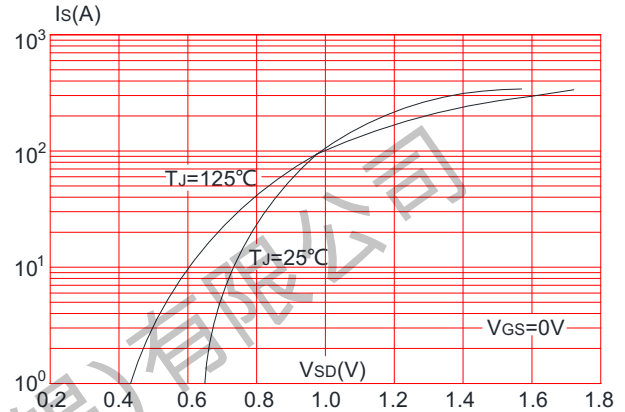


Figure 5: Gate Charge Characteristics

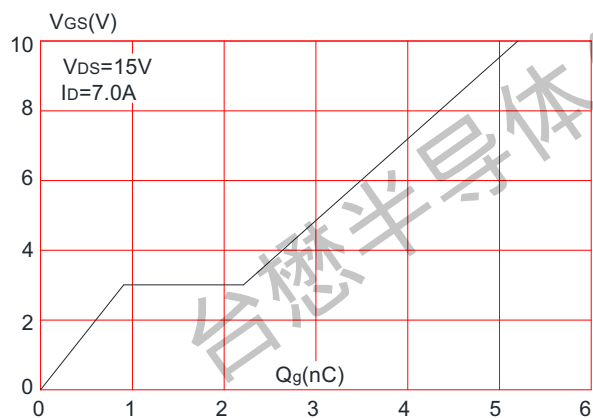
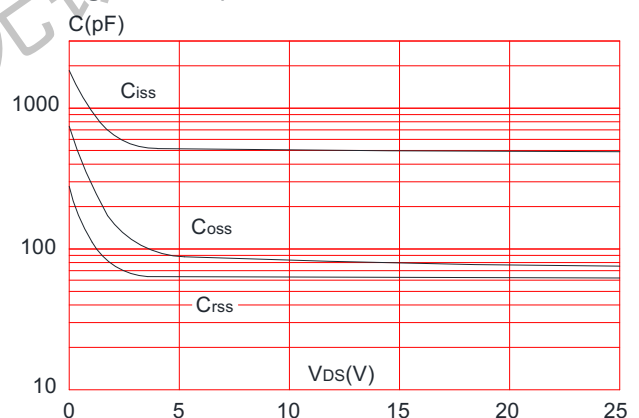


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

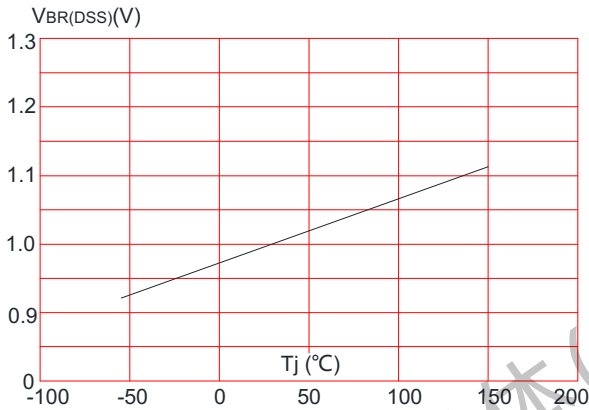


Figure 8: Normalized on Resistance vs. Junction Temperature

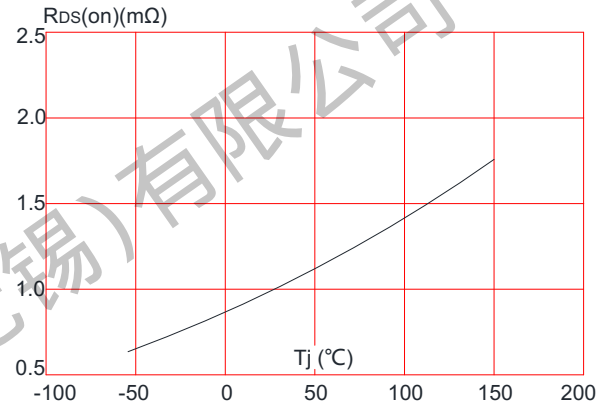


Figure 9: Maximum Safe Operating Area

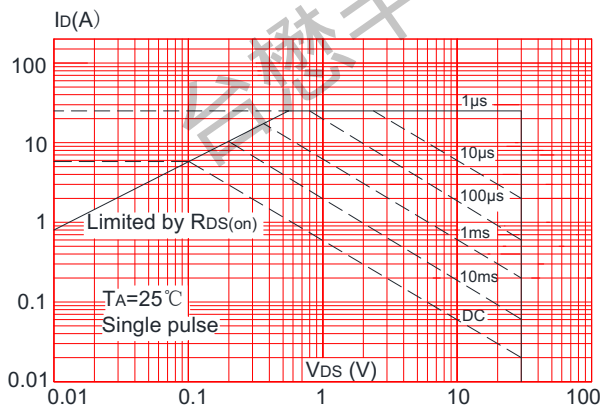


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

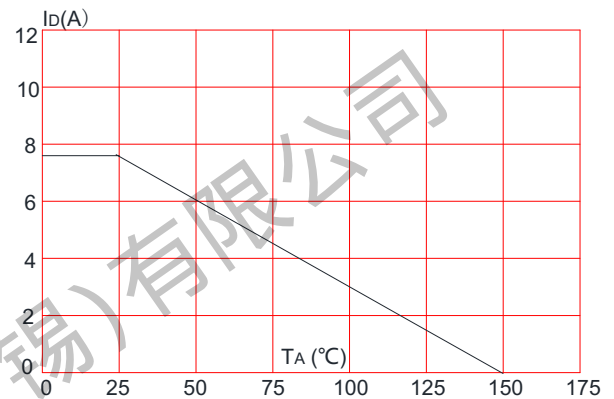
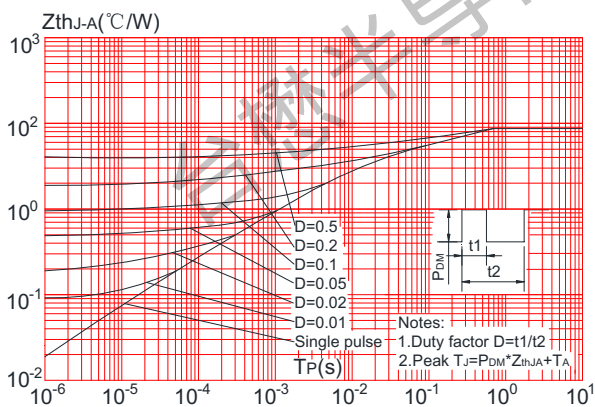


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

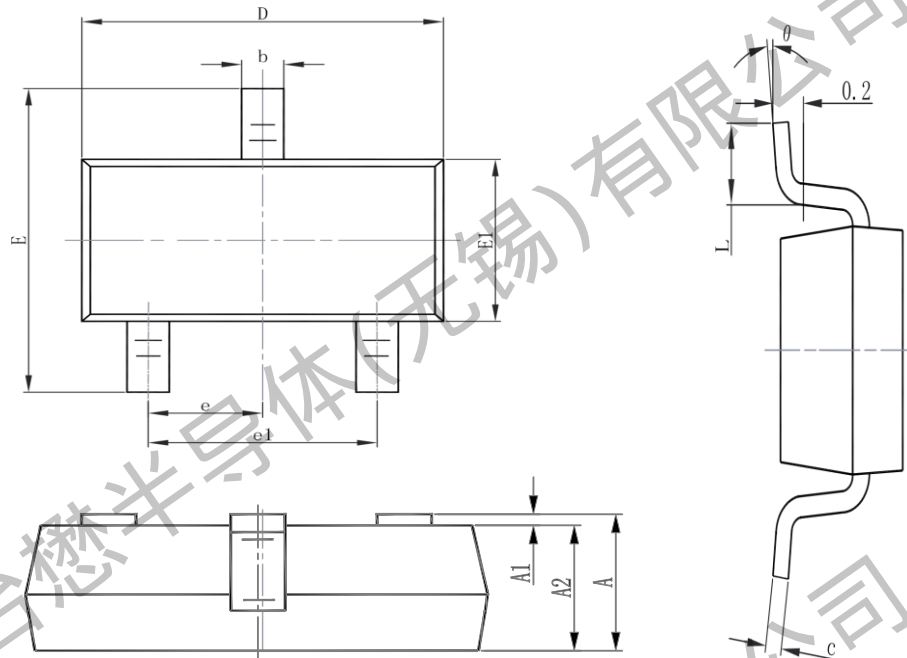




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Package Mechanical Data:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

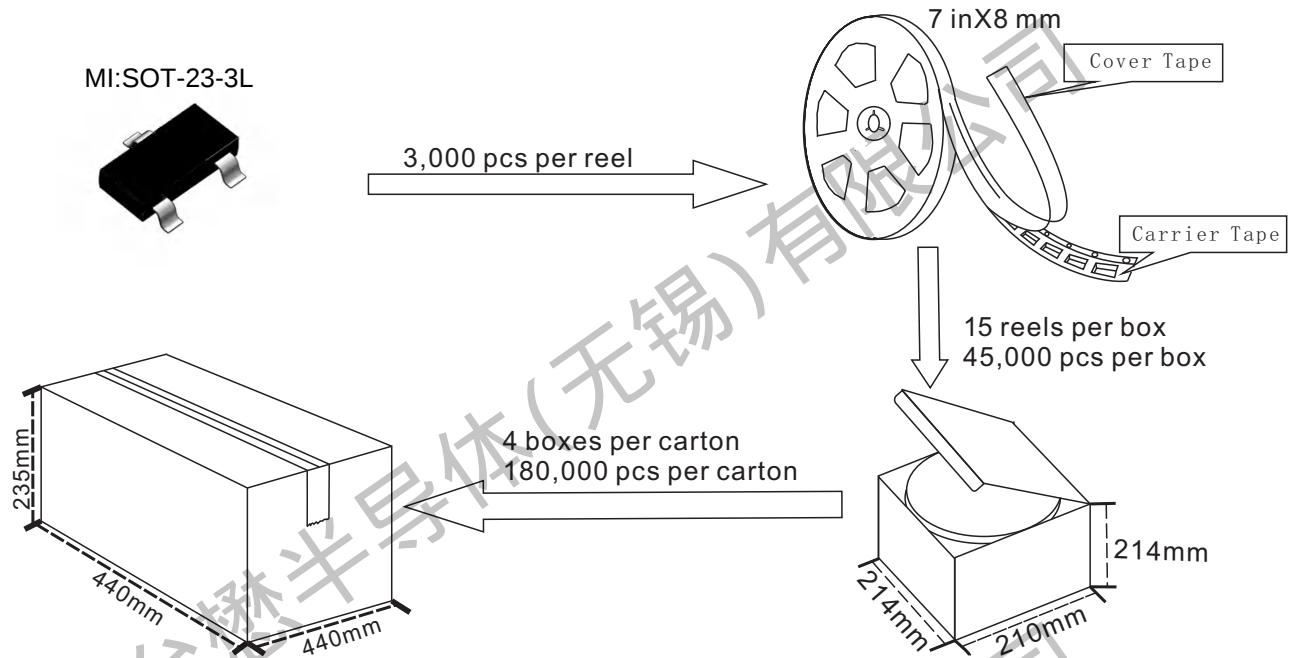


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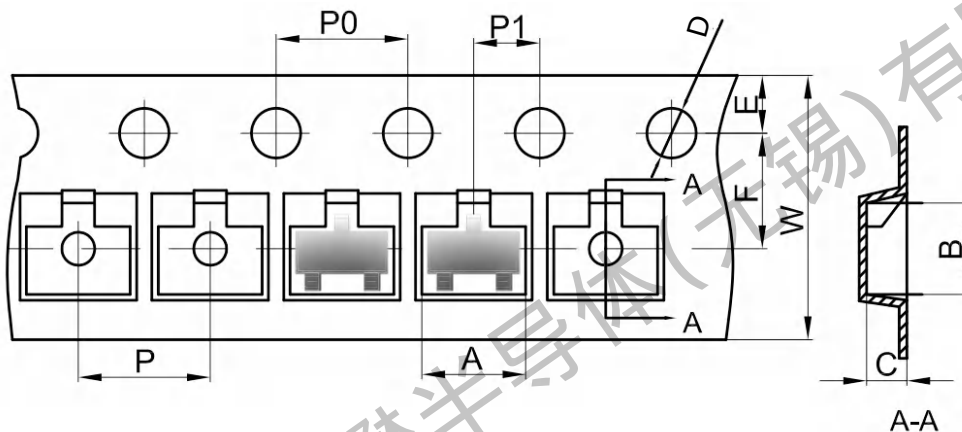
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SOT-23-3L Packing

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)



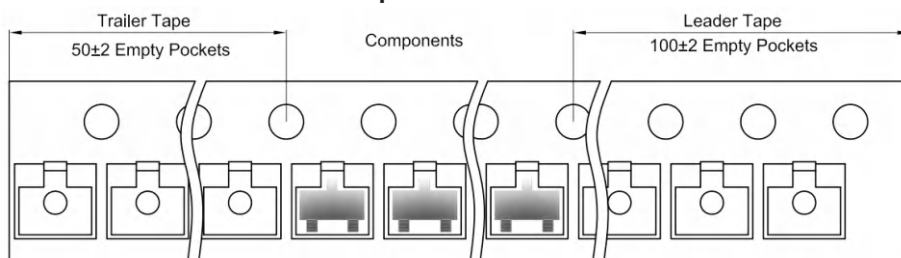
SOT-23-3L Embossed Carrier Tape



Dimensions are in millimeter

Pkg type	A	B	C	D	E	F	P0	P	P1	W
SOT-23-3L	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-3L Tape Leader and Trailer



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Revision history:

Date	Rev	Description	Page
2023.05.06	23.05	Original	